

8A, 600V - 1000V Standard Bridge Rectifier

FEATURES

- Glass passivated chip junction
- Ideal for automated placement
- UL Recognized File # E-326854
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

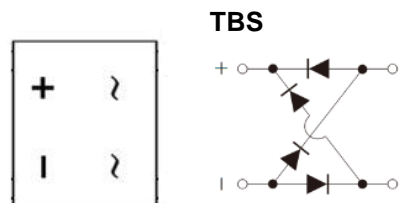
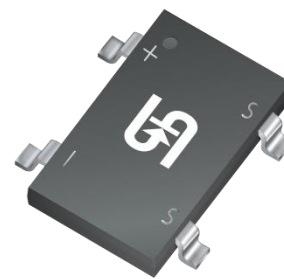
APPLICATIONS

- Switching mode power supply
- AC to DC

MECHANICAL DATA

- Case: TBS
- Molding compound meets UL 94V-0 flammability rating
- Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1 whisker test
- Polarity: As marked
- Weight: 0.380g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I_F	8	A
V_{RRM}	600 - 1000	V
I_{FSM}	200	A
T_{JMAX}	150	°C
Package	TBS	
Configuration	Quad	



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	TBS 806	TBS 808	TBS 810	UNIT
Marking code on the device		TBS806	TBS808	TBS810	
Repetitive peak reverse voltage	V_{RRM}	600	800	1000	V
Reverse voltage, total rms value	$V_{R(RMS)}$	420	560	700	V
Forward current	I_F	8			A
Surge peak forward current single half sine-wave superimposed on rated load per diode	$t = 8.3\text{ms}$	200			A
	$t = 1.0\text{ms}$	475			A
Rating of fusing ($t < 8.3\text{ms}$)	I^2t	166			A^2s
Junction temperature	T_J	-55 to +150			°C
Storage temperature	T_{STG}	-55 to +150			°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	TYP	UNIT
Junction-to-lead thermal resistance	$R_{\theta JL}$	13	°C/W
Junction-to-ambient thermal resistance	$R_{\theta JA}$	50	°C/W
Junction-to-case thermal resistance	$R_{\theta JC}$	9.2	°C/W

Thermal Performance Note: Units mounted on PCB (16mm x 16mm Cu pad test board)

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT
Forward voltage per diode ⁽¹⁾	$I_F = 4\text{A}, T_J = 25^\circ\text{C}$	V_F	0.90	-	V
	$I_F = 8\text{A}, T_J = 25^\circ\text{C}$		0.97	1.05	V
	$I_F = 4\text{A}, T_J = 125^\circ\text{C}$		0.81	-	V
	$I_F = 8\text{A}, T_J = 125^\circ\text{C}$		0.89	-	V
Reverse current @ rated V_R per diode ⁽²⁾	$T_J = 25^\circ\text{C}$	I_R	-	5	μA
	$T_J = 125^\circ\text{C}$		-	200	μA
Junction capacitance per diode	1MHz, $V_R = 4.0\text{V}$	C_J	66	-	pF

Notes:

1. Pulse test with PW = 0.3ms
2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE⁽¹⁾	PACKAGE	PACKING
TBS8x	TBS	1,800 / Tape & Reel

Notes:

1. "x" defines voltage from 600V(TBS806) to 1000V(TBS810)

CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

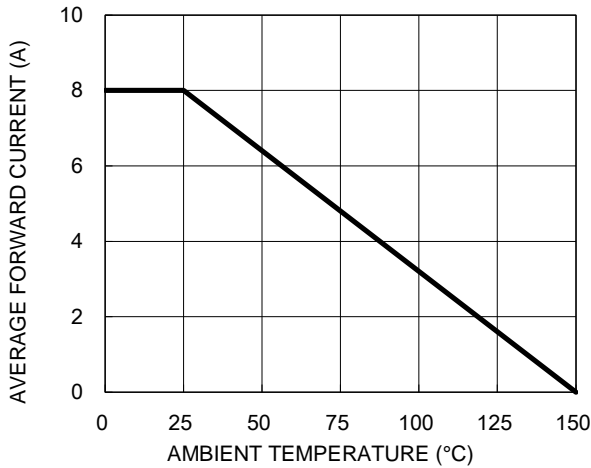


Fig.2 Typical Junction Capacitance

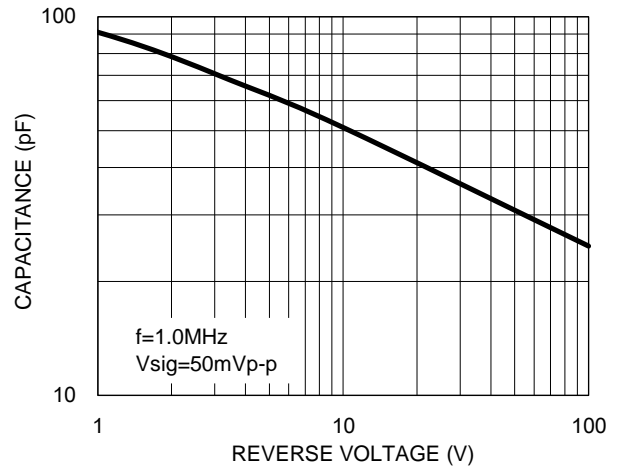


Fig.3 Typical Reverse Characteristics

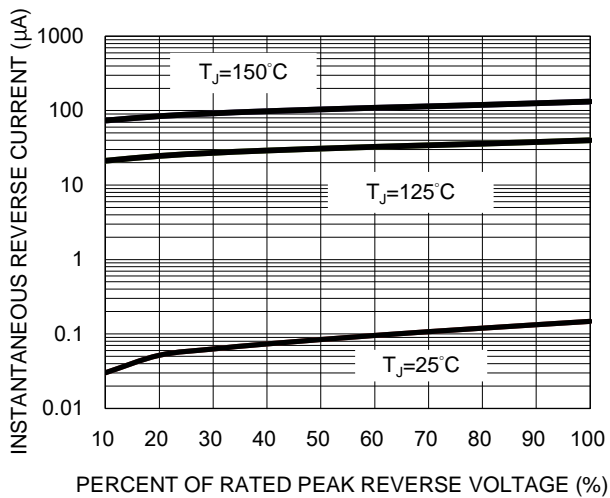
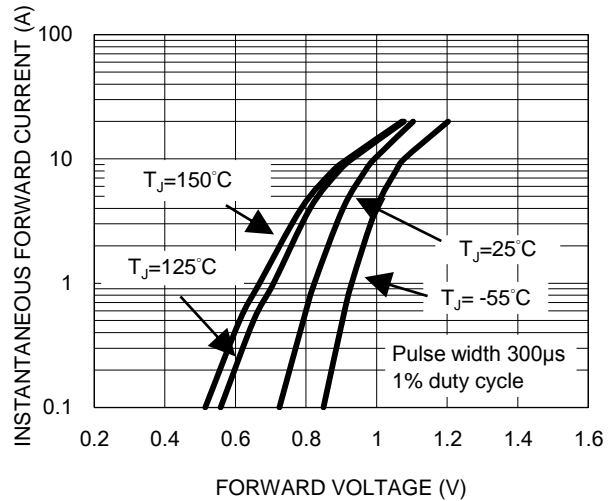
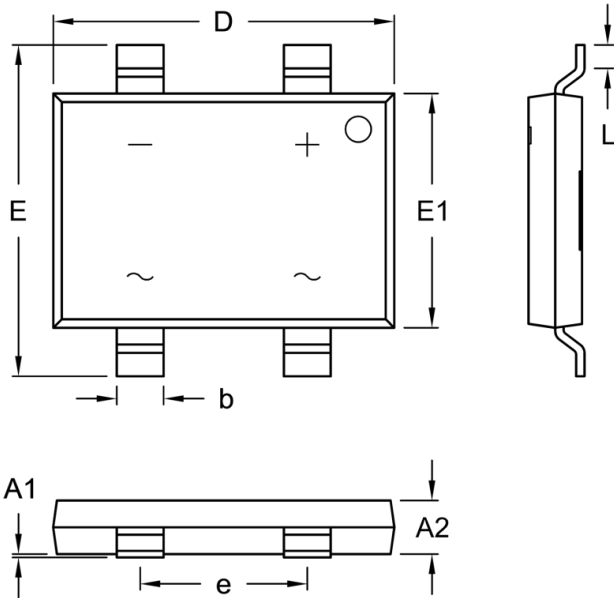


Fig.4 Typical Forward Characteristics



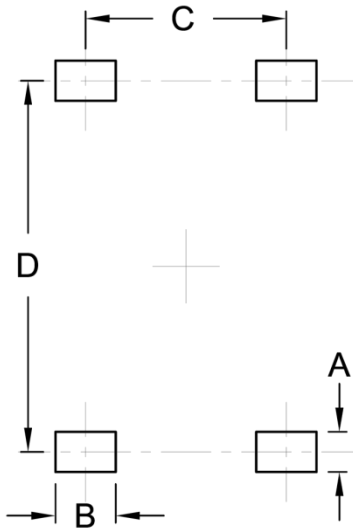
PACKAGE OUTLINE DIMENSIONS

TBS



DIM	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A1	0.00	0.15	0.000	0.006
A2	1.40	1.80	0.055	0.071
b	1.30	1.50	0.051	0.059
D	10.00	10.40	0.394	0.409
E	9.70	10.10	0.382	0.398
E1	6.80	7.20	0.268	0.283
e	4.90	5.10	0.193	0.201
L	0.50	1.10	0.020	0.043

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	1.00	0.039
B	1.50	0.059
C	5.00	0.197
D	9.25	0.364

MARKING DIAGRAM



P/N = Marking Code
 YW = Date Code
 F = Factory Code